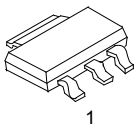
BCP68

NPN SILICON TRANSISTOR

NPN MEDIUM POWER TRANSISTOR



SOT-223

Lead-free: BCP68L
Halogen-free: BCP68G

■ FEATURES

* High current (max. 1 A)
* Low voltage (max. 20 V).
* Complementary to UTC BCP69

■ APPLICATIONS

* General purpose switching and amplification under high current conditions.

■ ORDERING INFORMATION

Ordering Number			Package	Pin Assignment			Packing
Normal	Lead Free Plating	Halogen Free		1	2	3	
BCP68-xx-AA3-R	BCP68L-xx-AA3-R	BCP68G-xx-AA3-R	SOT-223	B	C	E	Tape Reel

BCP68L-xx-AA3-R

(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) AA3: SOT-223
(3)Rank	(3) xx: refer to Classification of h_{FE}
(4)Lead Plating	(4) L: Lead Free Plating, Blank: Pb/Sn

■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-Base Voltage (Open Emitter)		V_{CBO}	32	V
Collector-Emitter Voltage (Open Base)		V_{CEO}	20	V
Emitter-Base Voltage (Open Collector)		V_{EBO}	5	V
Collector Current	DC	I_C	1	A
	Peak	I_{CM}	2	A
Peak Base Current		I_{BM}	200	mA
Total Power Dissipation (Ta ≤ 25℃)		P_D	1.35	W
Junction Temperature		T_J	150	℃
Operating Temperature		T_{OPR}	-45 ~ +150	℃
Storage Temperature		T_{STG}	-65 ~ +150	℃

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT
Thermal Resistance From Junction To Ambient	θ_{JA}	91	℃/W

■ ELECTRICAL CHARACTERISTICS (T_J = 25℃, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	I_C = 1A, I_B =100mA			500	mV
Base-Emitter Voltage	V_{BE}	I_C = 5mA, V_{CE} = 10V		620		mV
		I_C = 1A, V_{CE} = 1V			1	V
Collector Cut-off Current	I_{CBO}	I_E = 0, V_{CB} = 25V			100	nA
		I_E = 0, V_{CB} = 25V, T_J = 150℃			10	μA
Emitter Cut-off Current	I_{EBO}	I_C = 0, V_{EB} = 5V			100	nA
DC Current Gain	h_{FE}	I_C = 5mA, V_{CE} = 10V	50			
		I_C = 500mA, V_{CE} = 1V	85		375	
		I_C = 1A, V_{CE} = 1V	60			
Collector Capacitance	C_C	I_E = i_e = 0, V_{CB} = 5V, f = 1MHz		48		pF
Transition Frequency	f_T	I_C = -10mA, V_{CE} = -5V, f = 100MHz	40			MHz
DC Current Gain Ratio of the Complementary Pairs	$\frac{h_{FE1}}{h_{FE2}}$	$\|I_C\|$ = 0.5A, $\|V_{CE}\|$ = 1V			1.6	

■ CLASSIFICATION OF h_{FE}

RANK	16	25
RANGE	100~250	160~375

■ TYPICAL CHARACTERISTIC